

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRA1417-6H** is a Common Base Device Designed for Class C Amplifier Applications in L-Band FM Microwave Links.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	50 V
P_{DISS}	19 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	9.0 °C/W

PACKAGE STYLE .250 2L FLG (B)

1 = COLLECTOR 2 = BASE
3 = EMITTER

DIM	MILLIMETER	TOL	INCHES	TOL
A	9.40	.61	.370	.024
B	6.60	.18	.250	.005
C	9.40	.61	.370	.024
D	20.32	.25	.800	.010
E	14.22	.13	.560	.005
F	6.35	.13	.250	.005
G	0.10	.05	.004	.002
H	2.54	.13	.100	.005
I	1.27	.13	.050	.005
J	3.30 DIA	.13	.130 DIA	.005
K	3.43	.13	.135	.005
L	2.79	.13	.110	.005
M	1.52	.13	.060	.005

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 25 mA	50			V
BV_{CES}	I _C = 25 mA	55			V
BV_{EBO}	I _E = 3.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz		6.5		pF
P_G η_C	V _{CE} = 28 V P _{OUT} = 6.0 W f = 1400 - 1700 MHz	7.2	7.5 40		dB %